

P-Channel Enhancement Mode Power MOSFET

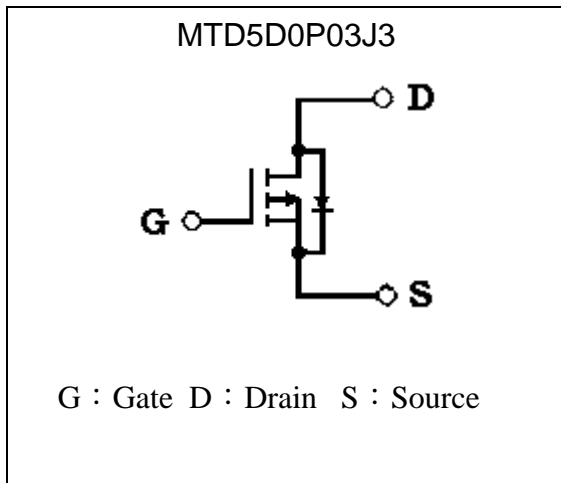
MTD5D0P03J3

BV_{DSS}	-30V
$I_D @ V_{GS}=-10V, T_C=25^{\circ}C$	-102A(silicon limit)
$R_{DSON} @ V_{GS}=-10V, I_D=-25A$	3.9m Ω (typ.)
$R_{DSON} @ V_{GS}=-6V, I_D=-10A$	5.6m Ω (typ.)

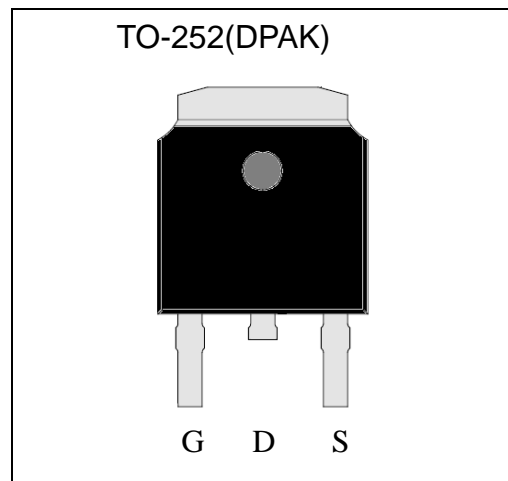
Features

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating & Halogen-free package

Equivalent Circuit

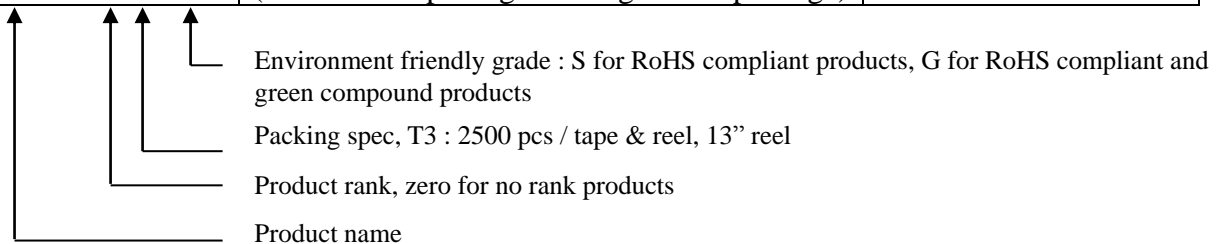


Outline



Ordering Information

Device	Package	Shipping
MTD5D0P03J3-0-T3-G	TO-252 (Pb-free lead plating & Halogen-free package)	2500 pcs / Tape & Reel





Absolute Maximum Ratings (T_c=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±25	
Continuous Drain Current @ V _{GS} =-10V, T _c =25°C (silicon limit)	I _D	-102	A
Continuous Drain Current @ V _{GS} =-10V, T _c =25°C (package limit)		-56	
Continuous Drain Current @ V _{GS} =-10V, T _c =100°C		-48	
Pulsed Drain Current (Note 1)	I _{DM}	-350	
Avalanche Current @ L=0.1mH	I _{AS}	-80	
Avalanche Energy @ L=0.5mH, I _D =-30A, V _{DD} =-15V (Note 2)	E _{AS}	225	mJ
Total Power Dissipation @ T _c =25°C	P _D	96	W
Total Power Dissipation @ T _c =100°C		38.4	
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55~+150	°C

Note : *1. Pulse width limited by maximum junction temperature

*2. 100% UIS testing in condition of V_D=-15V, L=0.5mH, V_G=-10V, I_D=-26A, Rated V_{DS}=-30V P-Channel

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	1.3	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{θJA}	50 (Note)	
		110	

Note : The value of R_{θJA} is measured with the device mounted on 1 in²FR-4 board with 2 oz. copper, in a still air environment with T_A=25 °C.

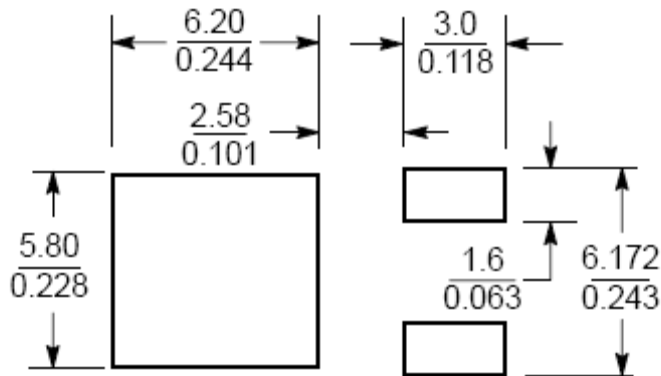
Characteristics (T_c=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-30	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-1.5	-	-3		V _{DS} =V _{GS} , I _D =-250μA
G _{FS} *1	-	32.2	-	S	V _{DS} =-10V, I _D =-20A
I _{GSS}	-	-	±100	nA	V _{GS} =±25V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-24V, V _{GS} =0V
	-	-	-10		V _{DS} =-24V, V _{GS} =0V, T _j =125°C
R _{DS(ON)} *1	-	3.9	5.5	mΩ	V _{GS} =-10V, I _D =-25A
	-	5.6	12		V _{GS} =-6V, I _D =-10A
Dynamic					
Q _g *1, 2	-	91	-	nC	V _{DS} =-15V, V _{GS} =-10V, I _D =-25A
Q _{gs} *1, 2	-	23.3	-		
Q _{gd} *1, 2	-	23.6	-		
t _{d(ON)} *1, 2	-	30	-	ns	V _{DS} =-15V, I _D =-25A, V _{GS} =-10V, R _G =1Ω
t _r *1, 2	-	24.2	-		
t _{d(OFF)} *1, 2	-	88.2	-		
t _f *1, 2	-	26.2	-		

Ciss	-	5607	-	pF	V _{GS} =0V, V _{DS} =-15V, f=1MHz
Coss	-	943	-		
Crss	-	429	-		
Rg	-	3.6	-	Ω	f=1MHz
Source-Drain Diode					
I _S *1	-	-	-56	A	
I _{SM} *3	-	-	-224		
V _{SD} *1	-	-0.83	-1.2	V	I _S =-25A, V _{GS} =0V
trr	-	31.2	-	ns	I _F =-25A, dI _F /dt=100A/μs
Qrr	-	24.7	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

Recommended soldering footprint

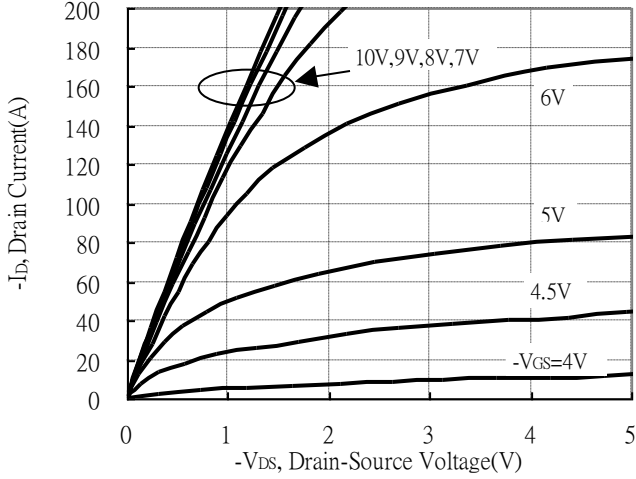


Unit ($\frac{\text{mm}}{\text{inch}}$)

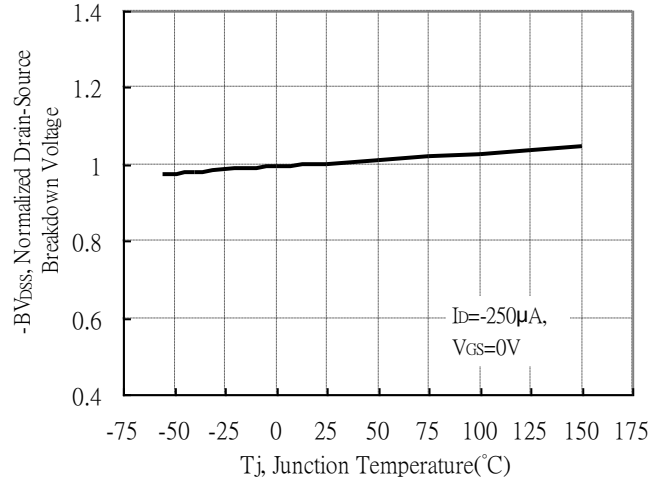


Typical Characteristics

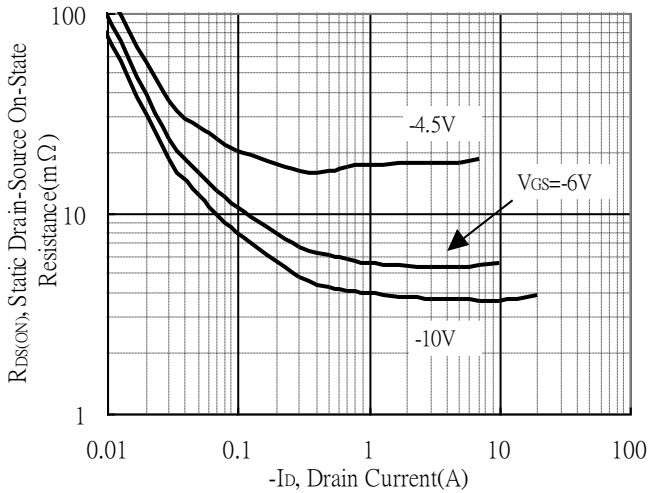
Typical Output Characteristics



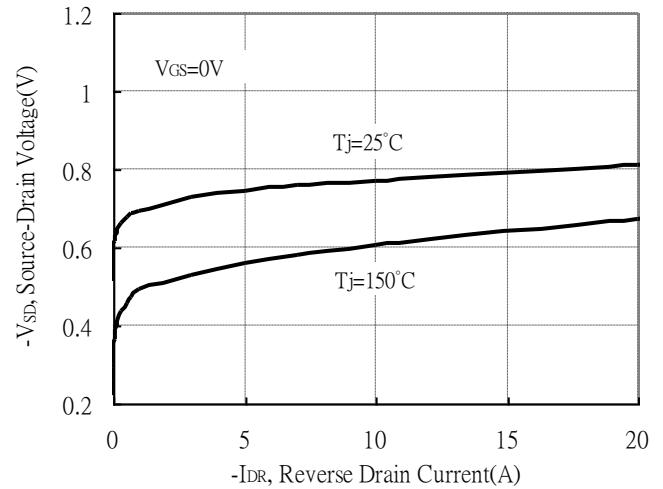
Brekdown Voltage vs Ambient Temperature



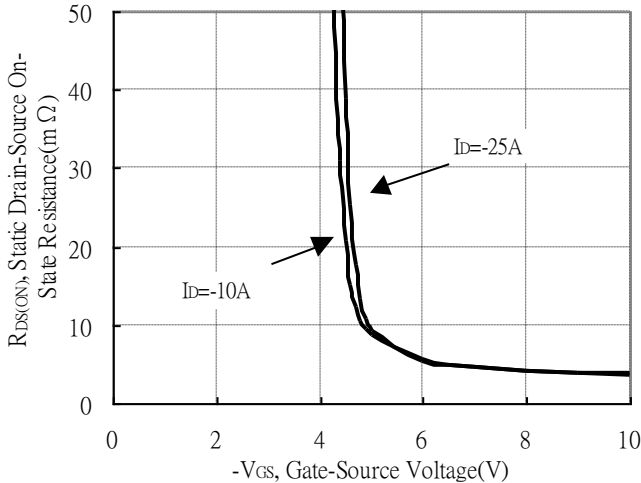
Static Drain-Source On-State resistance vs Drain Current



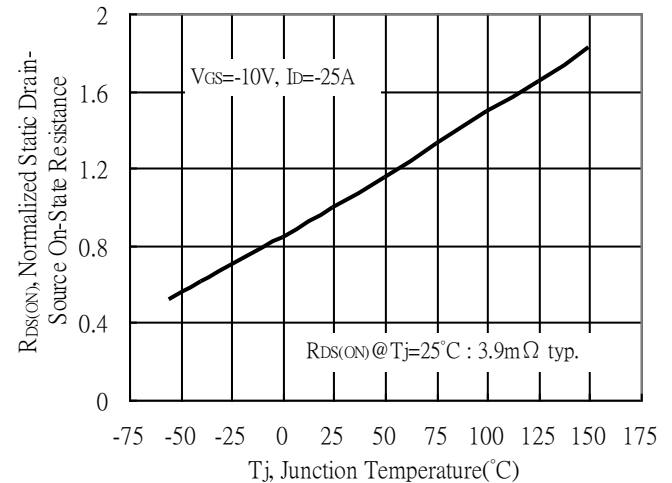
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

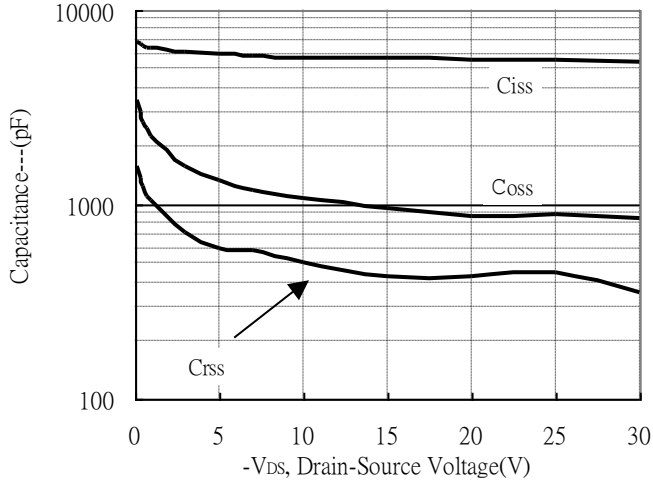


Drain-Source On-State Resistance vs Junction Temperature

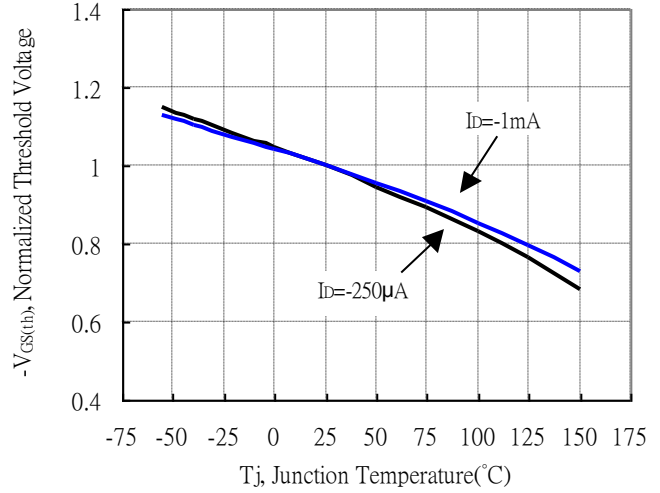


Typical Characteristics(Cont.)

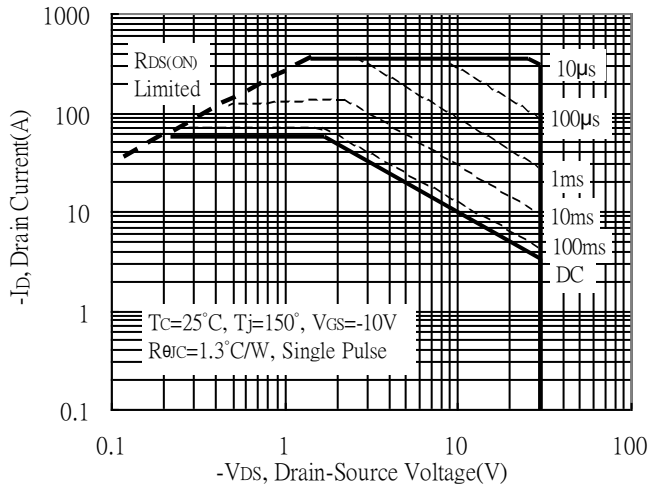
Capacitance vs Drain-to-Source Voltage



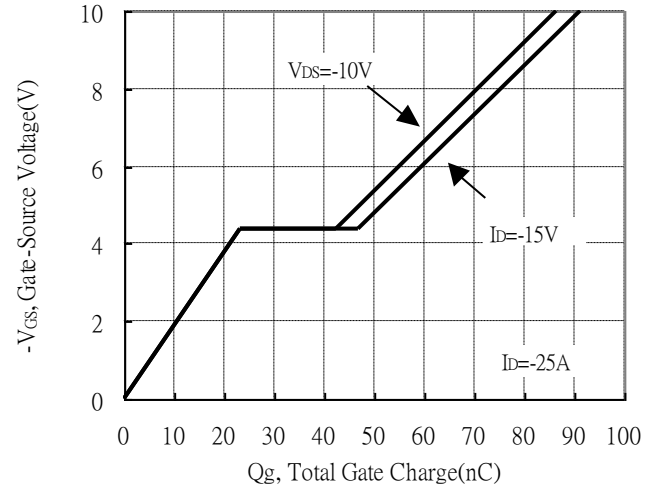
Threshold Voltage vs Junction Temperature



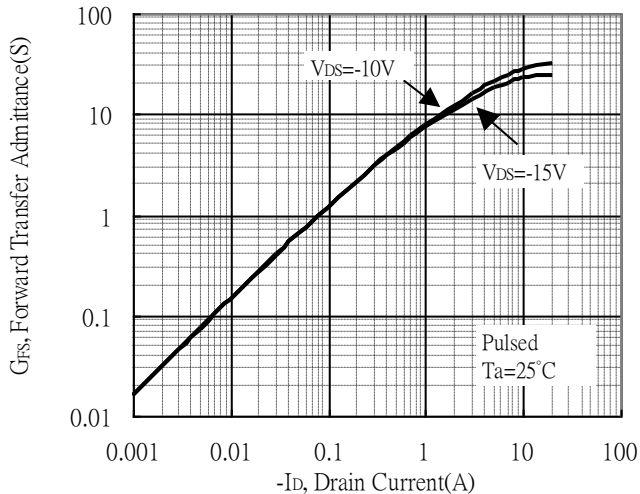
Maximum Safe Operating Area



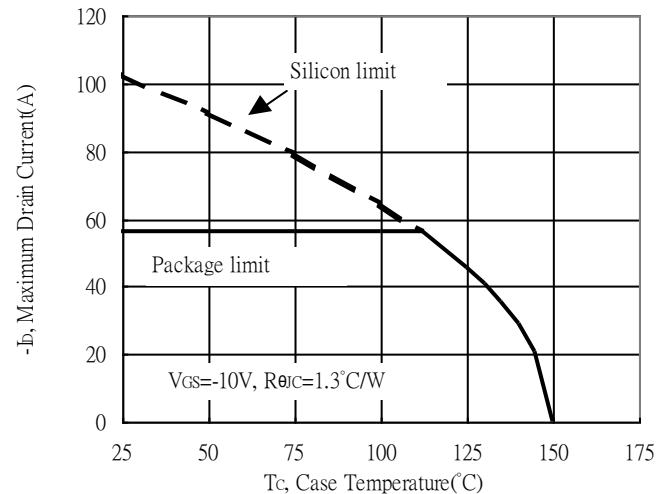
Gate Charge Characteristics



Forward Transfer Admittance vs Drain Current

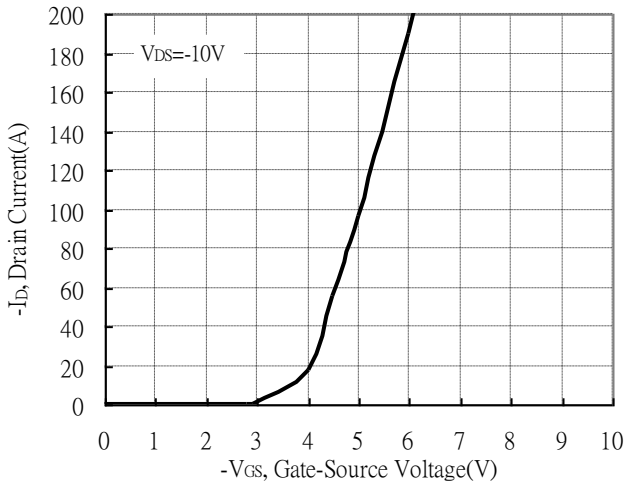


Maximum Drain Current vs Case Temperature

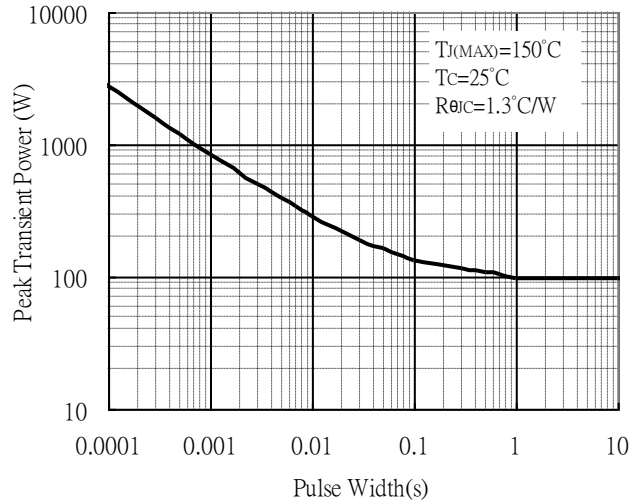


Typical Characteristics(Cont.)

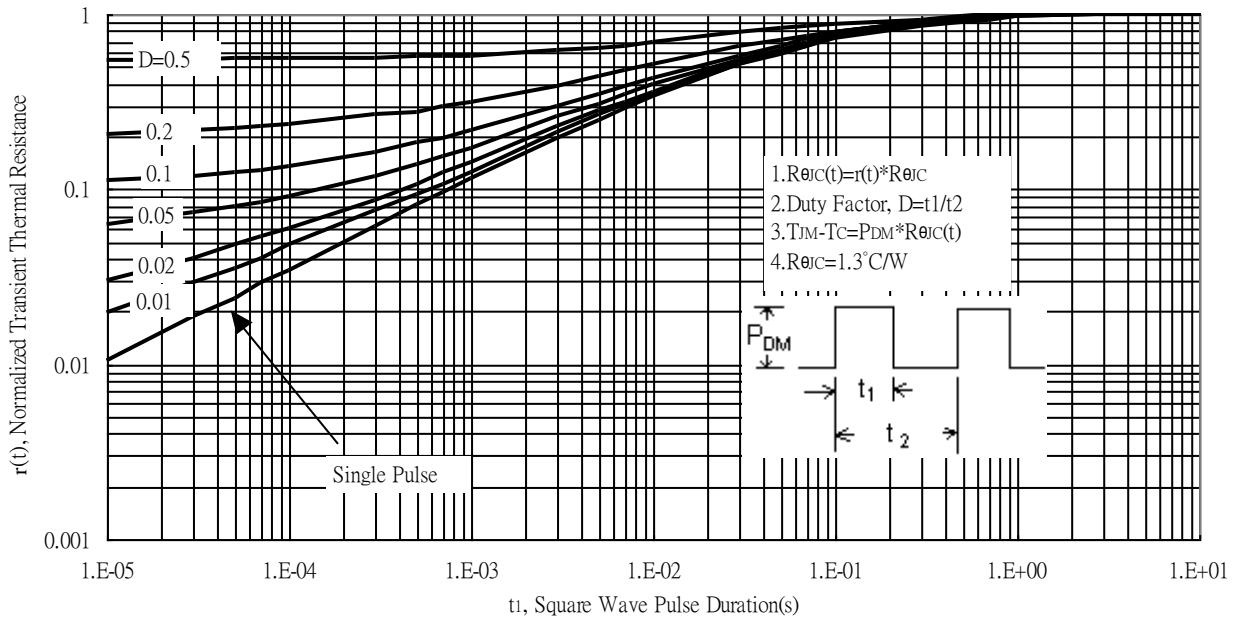
Typical Transfer Characteristics



Single Pulse Maximum Power Dissipation



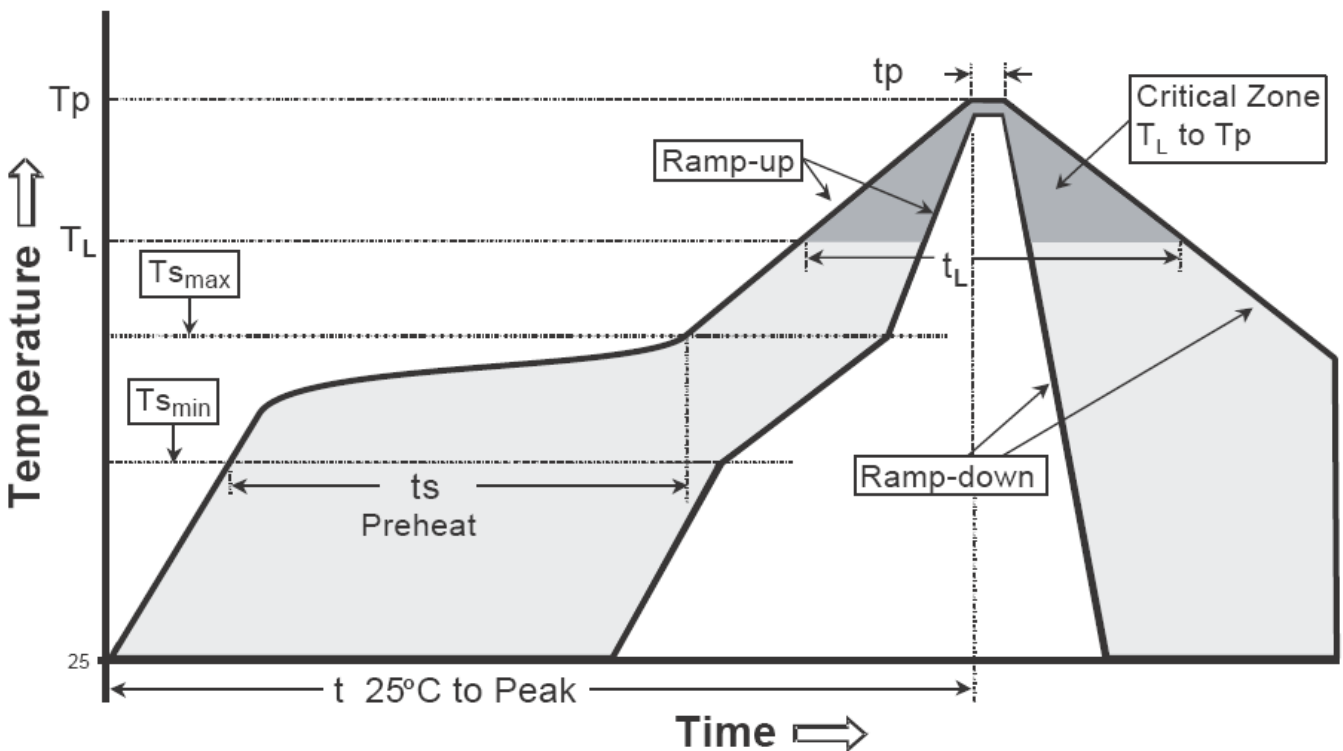
Transient Thermal Response Curves



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

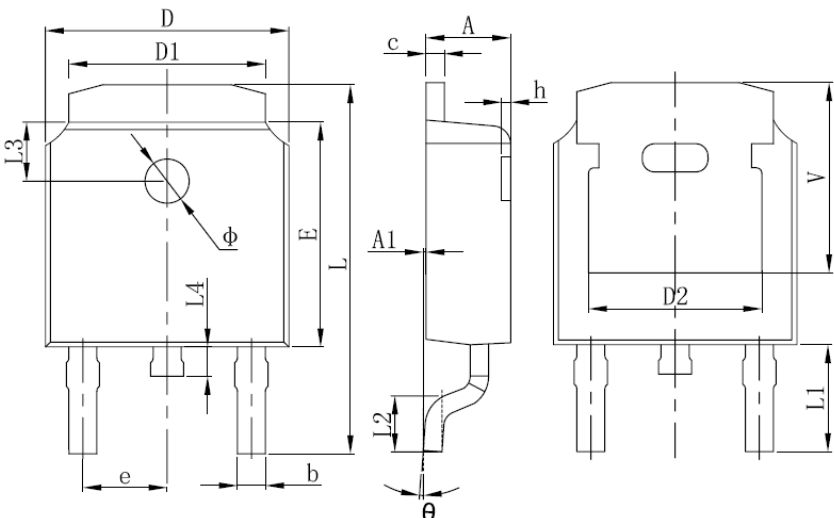
Recommended temperature profile for IR reflow



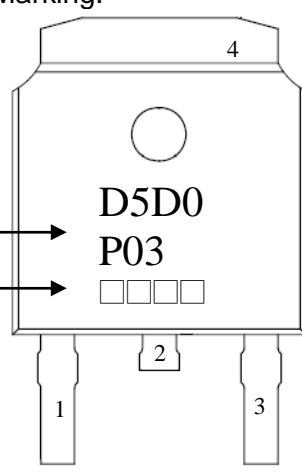
Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



Marking:



Device Code → D5D0
 Date Code → P03

3-Lead TO-252 Plastic Surface Mount Package
 CYStek Package Code: J3

Style: Pin 1.Gate 2.Drain 3.Source
 4.Drain

Date Code :
 First Code : Last digit of Christian Year
 Second Code : Month Code : Jan→A, Feb→B, Mar→C, Apr→D, May→E, Jun→F, Jul→G,
 Aug→H, Sep→J, Oct→K, Nov→L, Dec→M
 Last Two Codes : Production Serial Code, 01~99

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	L	0.382	0.406	9.712	10.312
A1	0.000	0.005	0.000	0.127	L1	0.114	REF	2.900	REF
b	0.025	0.030	0.635	0.770	L2	0.055	0.067	1.400	1.700
c	0.018	0.023	0.460	0.580	L3	0.063	REF	1.600	REF
D	0.256	0.264	6.500	6.700	L4	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	Φ	0.043	0.051	1.100	1.300
D2	0.190	REF	4.830	REF	θ	0°	8°	0°	8°
E	0.236	0.244	6.000	6.200	h	0.000	0.012	0.000	0.300
e	0.086	0.094	2.186	2.386	v	0.207	REF	5.250	REF

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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